

Description

The AR0511D3 is a 5V bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AR0511D3 has a low capacitance with a typical value at 1pF, and complies with the IEC 61000-4-2 (ESD) with ±30kV air and ±30kV contact discharge. It is assembled into a lead-free SOD-323 package. The small size, low capacitance and high ESD surge protection make AR0511D3 an ideal choice to protect cell phone, wireless systems, and communication equipment.

Features

- 360W peak pulse power (8/20µs)
- Ultra low capacitance: 1pF typical
- Ultra low leakage: nA level
- Operating voltage: 5V
- Low clamping voltage
- Protects one power line or data line
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test

Air discharge: ±30kV Contact discharge: ±30kV

- IEC61000-4-5 (Lightning) 18A (8/20µs)

RoHS Compliant

Mechanical Characteristics

Package: SOD-323

Lead Finish: Matte Tin

• Case Material: "Green" Molding Compound.

• Moisture Sensitivity: Level 3 per J-STD-020

Terminal Connections: See Diagram Below

Marking Information: See Below

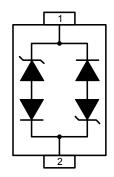
Applications

- USB Ports
- Smart Phones
- Wireless Systems
- Ethernet 10/100/1000 Base T

Marking Information



Dimensions and Pin Configuration



Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
AR0511D3	3000/Tape & Reel	7 inch

www.appliedpowermicro.com



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

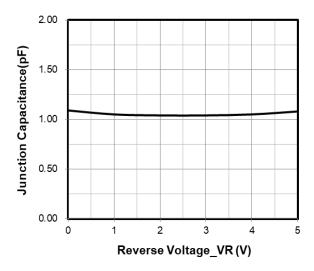
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20µs)	Ppk	360	W
Peak Pulse Current (8/20µs)	IPP	18	Α
ESD per IEC 61000-4-2 (Air)	1/505	±30	kV
ESD per IEC 61000-4-2 (Contact)	VESD	±30	
Operating Temperature Range	TJ	−55 to +125	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Electrical Characteristics (T_A=25°C unless otherwise specified)

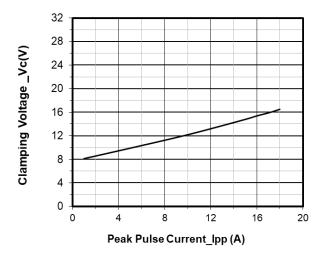
Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	VBR	6			V	IT = 1mA
Reverse Leakage Current	I _R			0.2	μA	VRWM = 5V
Clamping Voltage	Vc			10	V	IPP = 1A (8 x 20μs pulse)
Clamping Voltage	Vc			20	V	IPP = 18A (8 x 20µs pulse)
Junction Capacitance	Cı		1		pF	VR = 0V, f = 1MHz



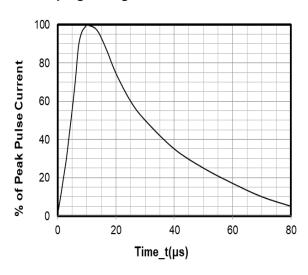
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



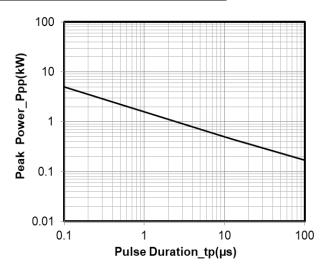
Junction Capacitance vs. Reverse Voltage



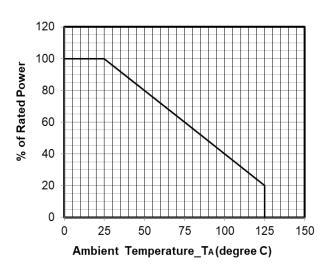
Clamping Voltage vs. Peak Pulse Current



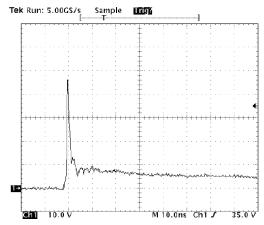
8 X 20µs Pulse Waveform



Peak Pulse Power vs. Pulse Time



Power Derating Curve

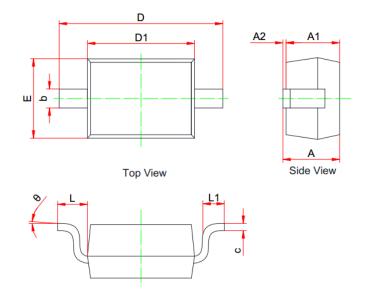


Note: Data is taken with a 10x attenuator

ESD Clamping Voltage 8 kV Contact per IEC61000-4-2

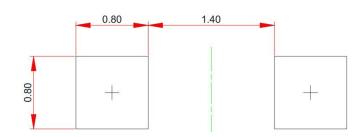


SOD-323 Package Outline Drawing



	MILLIMETERS				
SYM	MIN	NOM	MAX		
Α	0.800		1.100		
A1	0.800		0.900		
A2	0.000		0.100		
b	0.250		0.400		
С	0.080		0.177		
D1	1.600	1.700	1.800		
D	2.300		2.800		
Е	1.150		1.400		
L	0.475REF				
L1	0.100		0.500		
Θ	0°		8°		

Suggested Land Pattern



Unit: mm

Contact Information

Applied Power Microelectronics Co., Ltd.

Website: http://www.appliedpowermicro.com

Email: sales@appliedpowermicro.com

Phone: +86 (0519) 8399 3606

Applied Power Microelectronics Co., Ltd. (APM) reserves the right to make changes to the product specification and data in this document without notice. APM makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does APM assume any liability arising from the application or use of any products or circuits, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.